

isc N-Channel MOSFET Transistor

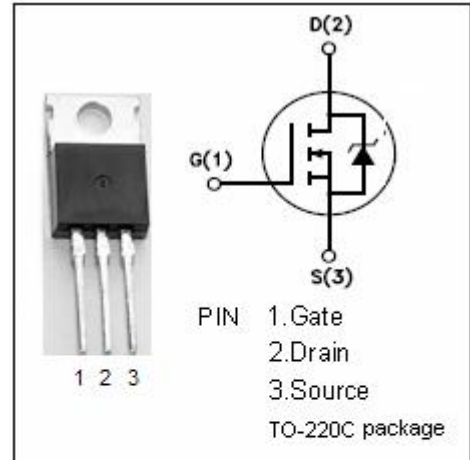
BUK454-200

DESCRIPTION

- High speed switching
- Easy driver for cost effective application

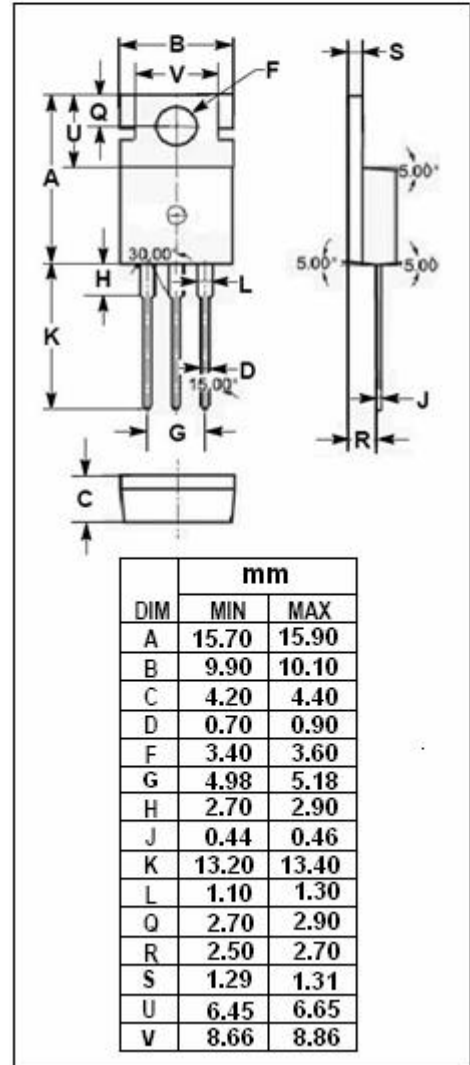
APPLICATIONS

- use in Switched Mode Power Supplies (SMPS), motor control, welding, And in general purpose switching resistance application



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	200	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current-continuous@ TC=37°C	9.2	A
P _{tot}	Total Dissipation@TC=25°C	90	W
T _j	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	1.47	°C/W
R _{th j-a}	Thermal Resistance,Junction to Ambient	60	°C/W

isc N-Channel Mosfet Transistor**BUK454-200****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	200		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.1	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 3.5A		0.4	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V; V _{GS} = 0		20	uA
V _{SD}	Diode Forward Voltage	I _F = 9.2A; V _{GS} = 0		1.5	V